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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/720,408	11/24/2003	Cha Deok Dong	29936/39763	4107	
4743 7	590 04/04/2005		EXAMINER		
	, GERSTEIN & BOR	WILSON, CHRISTIAN D			
6300 SEARS TOWER 233 S. WACKER DRIVE CHICAGO, IL 60606			ART UNIT	PAPER NUMBER	
			2891		
			DATE MAILED: 04/04/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

<u> </u>							
		Application No.	Applicant(s)				
		10/720,408	DONG ET AL.				
	Office Action Summary	Examiner	Art Unit				
		Christian Wilson	2891				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
THE - Exte after - If the - If NC - Failt Any	ORTENED STATUTORY PERIOD FOR REIMAILING DATE OF THIS COMMUNICATIOnsions of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory per ure to reply within the set or extended period for reply will, by stareply received by the Office later than three months after the may be patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no event, however, may a reply reply within the statutory minimum of thirty (3 iod will apply and will expire SIX (6) MONTH tute, cause the application to become ABAN	to be timely filed  O) days will be considered timely.  S from the mailing date of this communi  DONED (35 U.S.C. § 133).	ication.			
Status							
1)□	Responsive to communication(s) filed on	<del>,</del>					
2a)□	This action is <b>FINAL</b> . 2b) This action is non-final.						
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims							
5)□ 6)⊠ 7)□	<ul> <li>Claim(s) 1-5 is/are pending in the application.</li> <li>4a) Of the above claim(s) is/are withdrawn from consideration.</li> <li>□ Claim(s) is/are allowed.</li> <li>□ Claim(s) 1-5 is/are rejected.</li> <li>□ Claim(s) is/are objected to.</li> <li>□ Claim(s) are subject to restriction and/or election requirement.</li> </ul>						
Applicat	ion Papers						
<ul> <li>9) The specification is objected to by the Examiner.</li> <li>10) The drawing(s) filed on 24 November 2003 is/are: a) accepted or b) objected to by the Examiner.         Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).     </li> </ul>							
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.							
Priority (	under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  a) All b) Some * c) None of:  1. Certified copies of the priority documents have been received.  2. Certified copies of the priority documents have been received in Application No  3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  * See the attached detailed Office action for a list of the certified copies not received.							
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Attachmen							
2)  Notice 3) Information	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/ er No(s)/Mail Date		fail Date mal Patent Application (PTO-152)				

## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1 5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kim et al. in view of Liang et al.

Kim et al. (US 6,620,681) teaches a method of forming a floating gate of a flash memory device comprising the steps of providing a semiconductor substrate 100 with a tunnel oxide film 101 and first polysilicon film 103, forming a buffer oxide film 105 and a pad nitride film 107, forming a trench 109 in the substrate, depositing a device isolation oxide film 112, performing a planarization process using the pad nitride film as a barrier [Figure 2F], performing a strip process to remove the pad nitride film and part of the buffer oxide film at the same time [column 8, lines 40-45], removing the buffer oxide film using a cleaning process [column 8, lines 40-45], and depositing a second polysilicon film 126 which is patterned to form a floating gate with the first polysilicon film [column 8, lines 45-55]. Kim et al. does not discuss how much of the buffer oxide film is removed during the strip process. Liang et al. (US 6,326,283) teaches an STI forming method where at least 50% of the buffer oxide film is removed with the nitride film during a phosphoric stripping process [column 3, lines 5-10]. It would have been obvious to one of ordinary skill in the art to remove at least 50% of the buffer oxide film of Kim et al. during the

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strip process since Liang *et al.* teaches that while protecting the underlying layers during the stripping process the majority of the buffer oxide layer may be removed in one process step which reduces the process complexity.

Regarding claim 2, Kim et al. further teaches a buffer oxide layer with a thickness of 30 to 40 Å [column 5, line 63].

Regarding claim 3, Kim *et al.* further teaches a buffer oxide layer formed by plasma enhanced chemical vapor deposition [column 5, line 67]. Kim *et al.* also teaches a PECVD process using TEOS [column 7, lines 60-65]. It would have been obvious to one of ordinary skill in the art to use the PECVD method of Kim *et al.* with TEOS since this is a well known CVD material to deposit for good deposition characteristics.

Regarding claims 4 and 5, Kim et al. further teaches a wall oxide film 110 formed at a temperature in the range of 800 to 1000 °C

## Conclusion

- 3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. The cited prior art teaches method of forming flash memories with STI.
- 4. A copy of the EAST search history is enclosed.
- 5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Christian Wilson whose telephone number is (571) 272-1886. The examiner can normally be reached on weekdays, 7:30 AM to 4 PM.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Bill Baumeister can be reached on (571) 272-1722. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Christian Wilson, Ph.D.

**Primary Examiner** Art Unit 2891

CDW